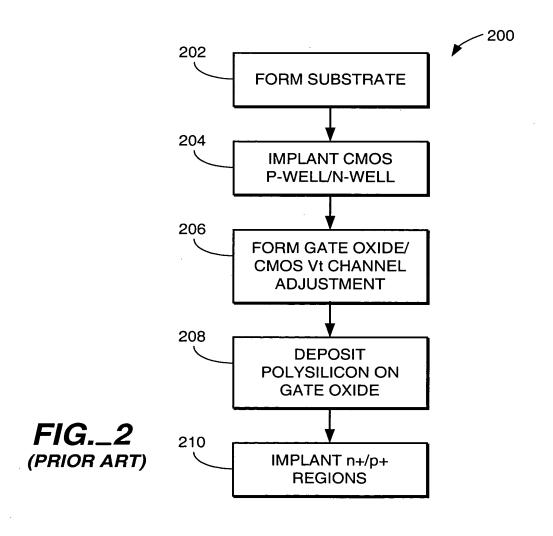
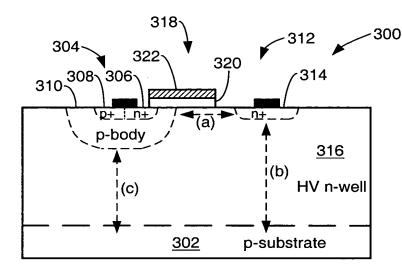


FIG.\_1 (PRIOR ART)

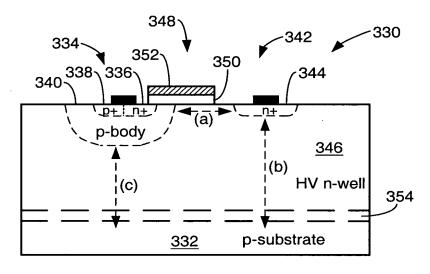


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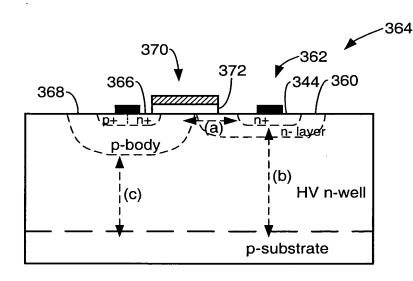
P-Body implanted after gate formation disrupts CMOS thermal budget

> FIG.\_3A (PRIOR ART)



P-Body implanted after gate formation disrupts CMOS thermal budget

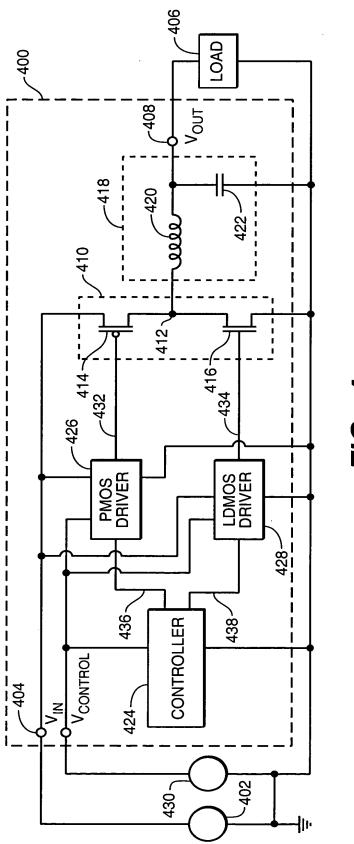
> FIG.\_3B (PRIOR ART)



P-Body implanted after gate formation disrupts CMOS thermal budget

> FIG.\_3C (PRIOR ART)

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F/G.\_4

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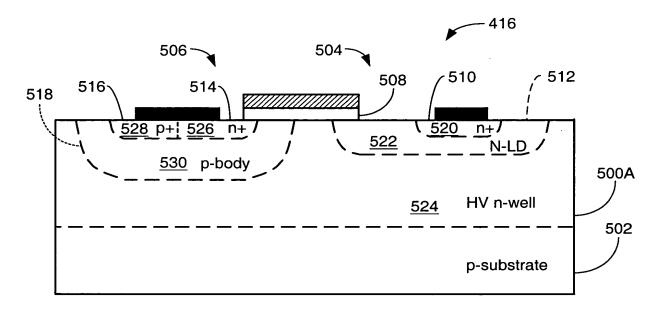


FIG.\_5A

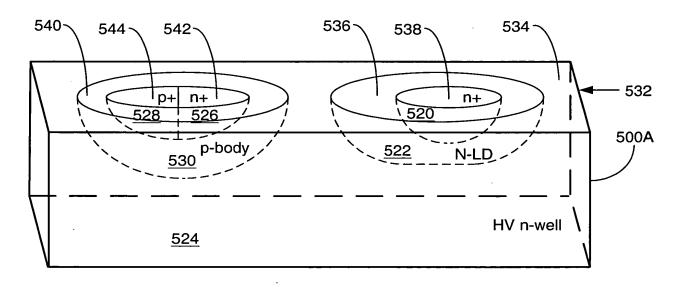
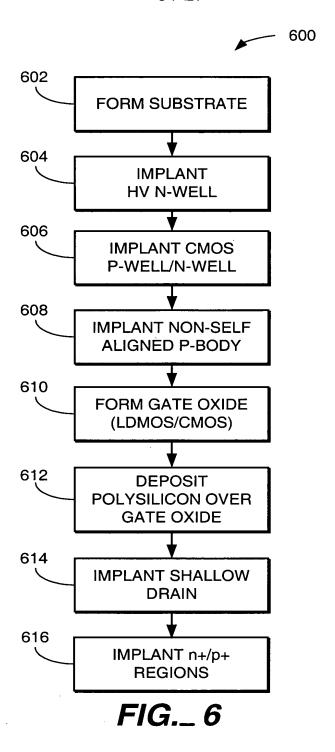
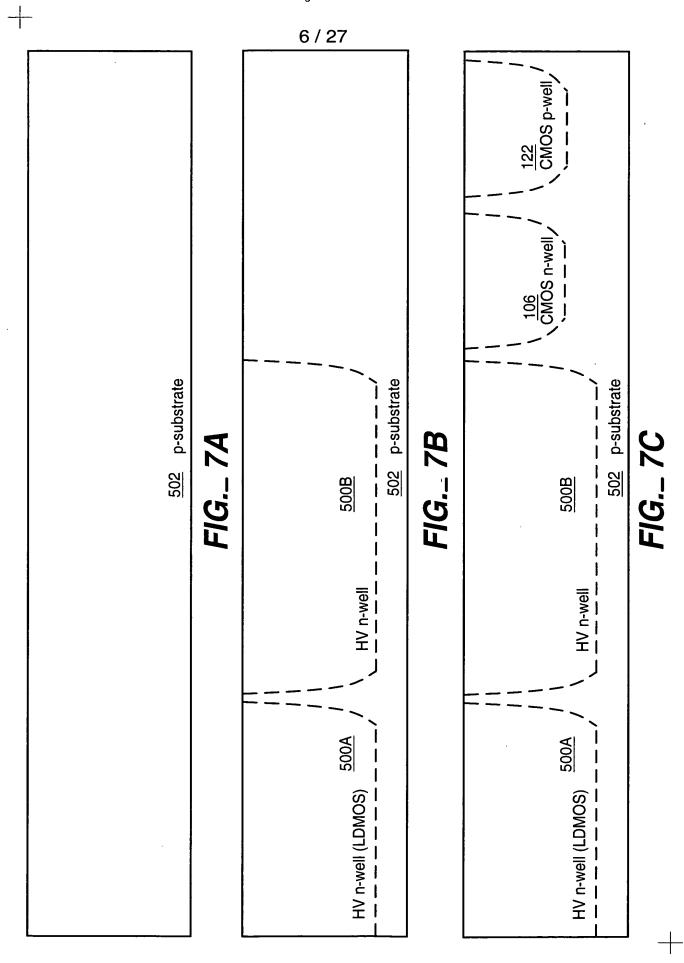


FIG.\_5B

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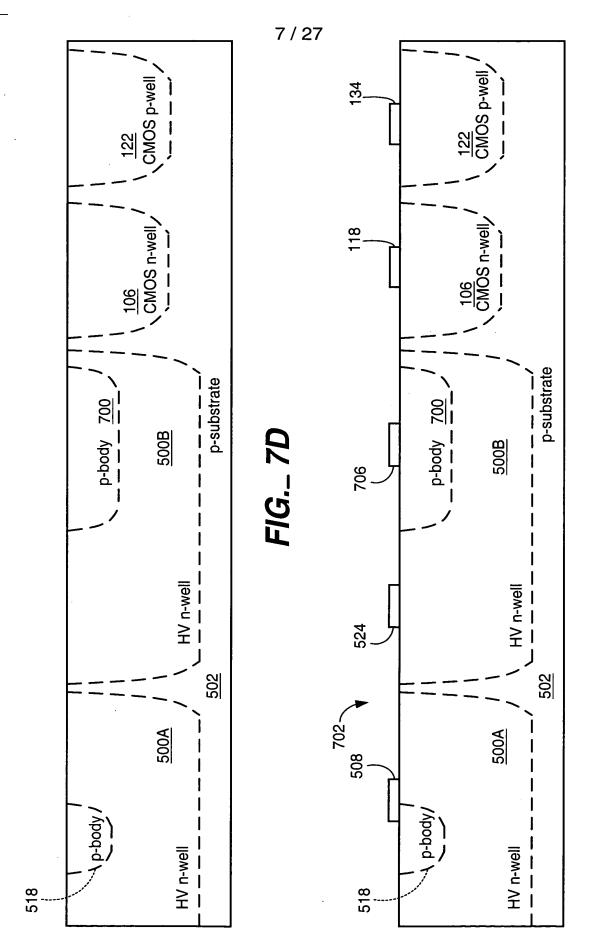
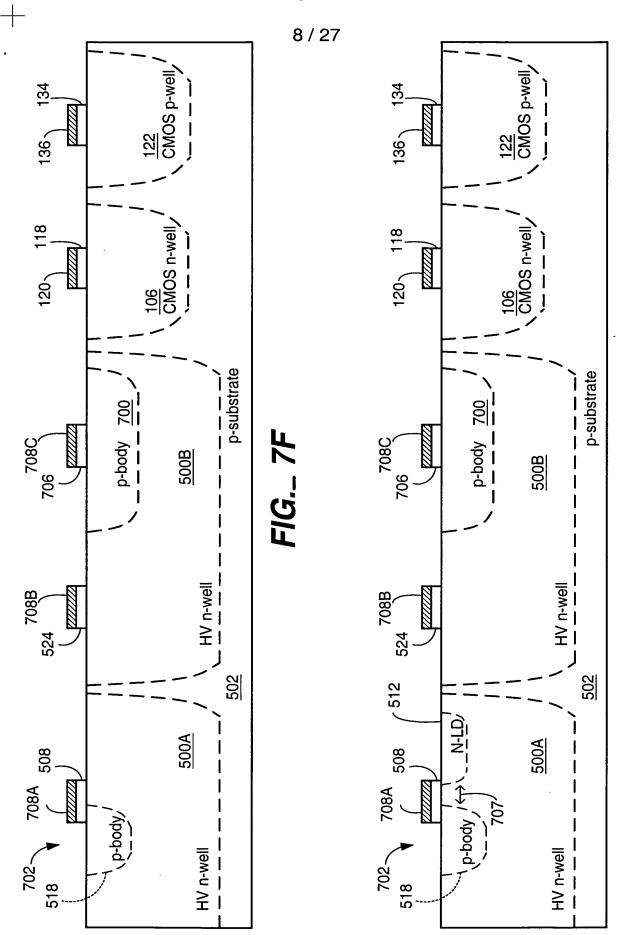


FIG.\_ 7E



F/G.\_ 7G



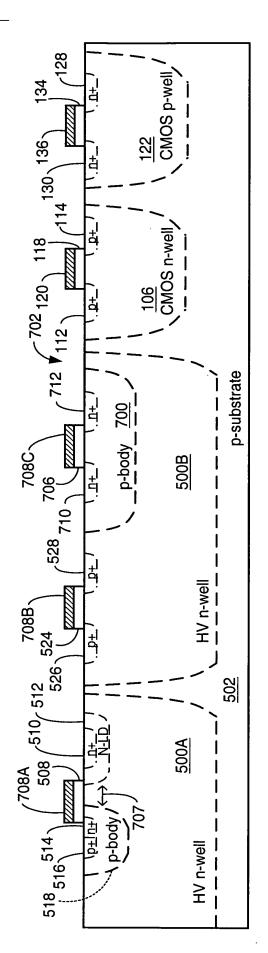


FIG.\_7H

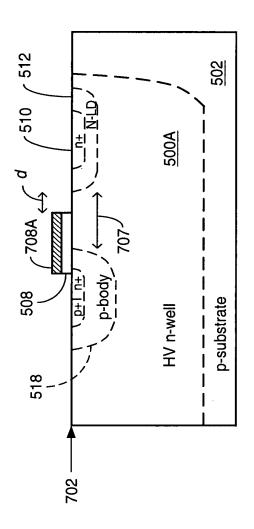
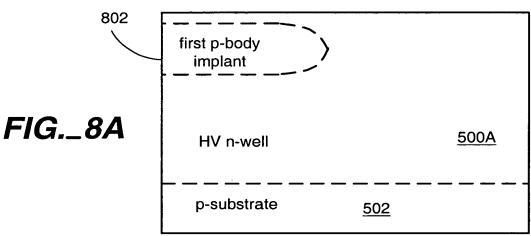
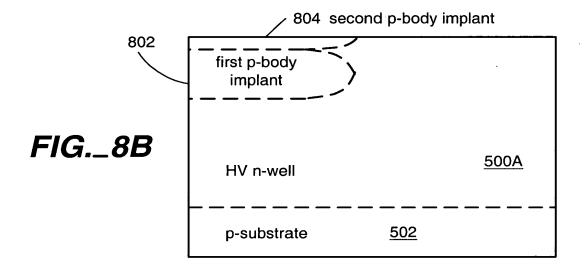
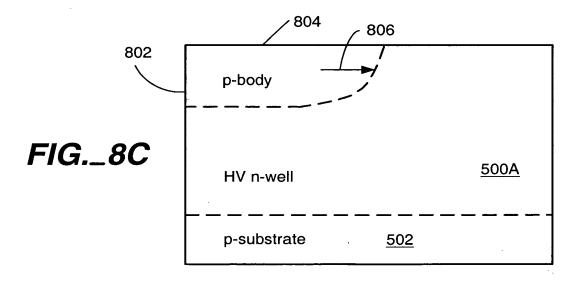


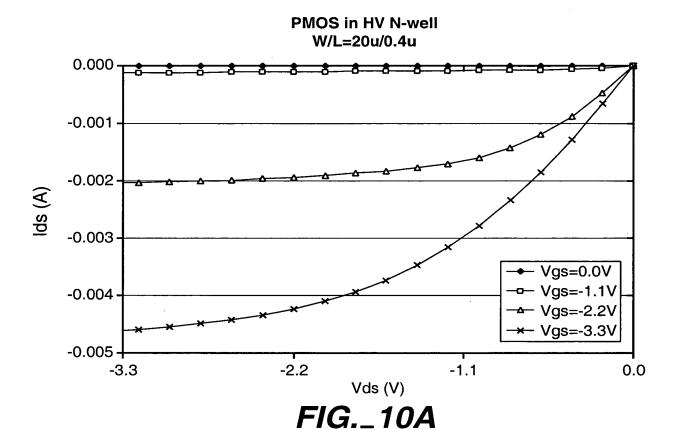
FIG.\_ 9



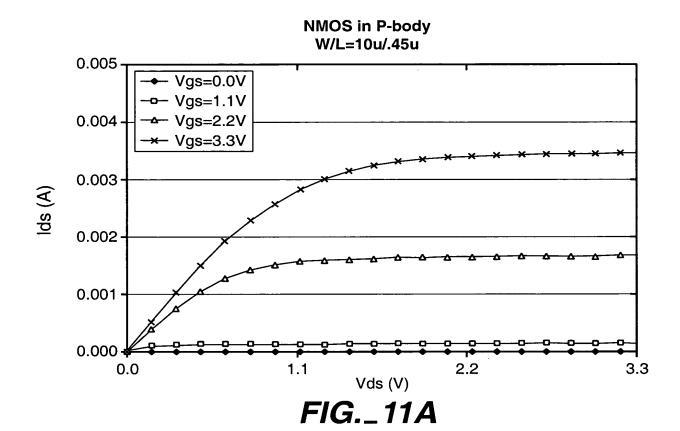


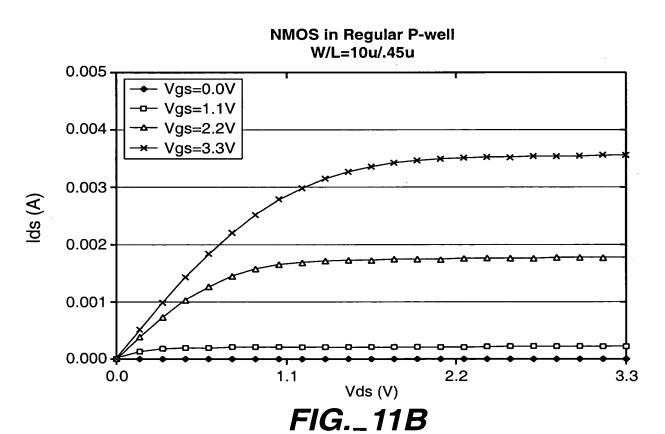






**PMOS in Regular N-well** W/L=20u/0.4u 0.00E+00 ---1.00E-03 -2.00E-03 lds (A) -3.00E-03 --- Vgs=-1.1V -4.00E-03 <del>×</del> Vgs=-3.3V -5.00E-03--2.2 -1.1 -3.3 0.0 Vds (V) FIG.\_10B





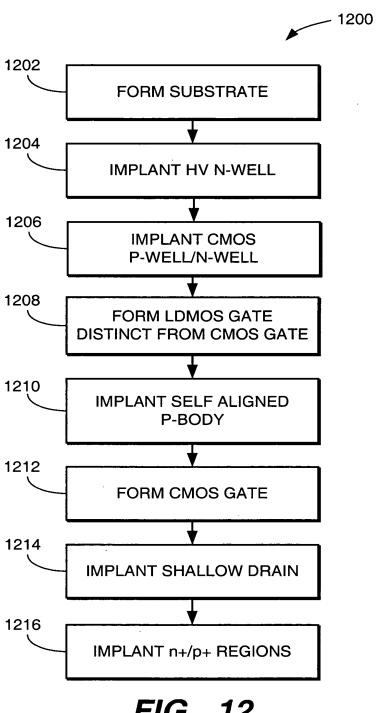
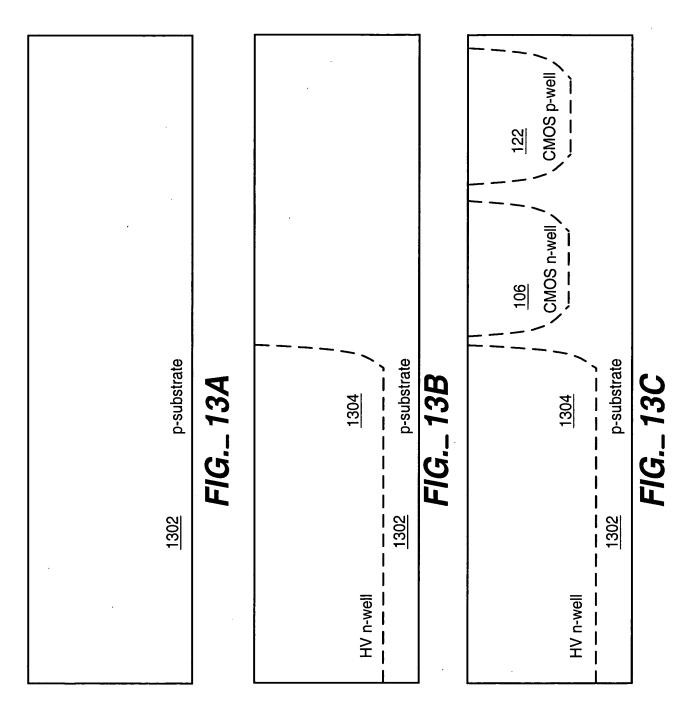
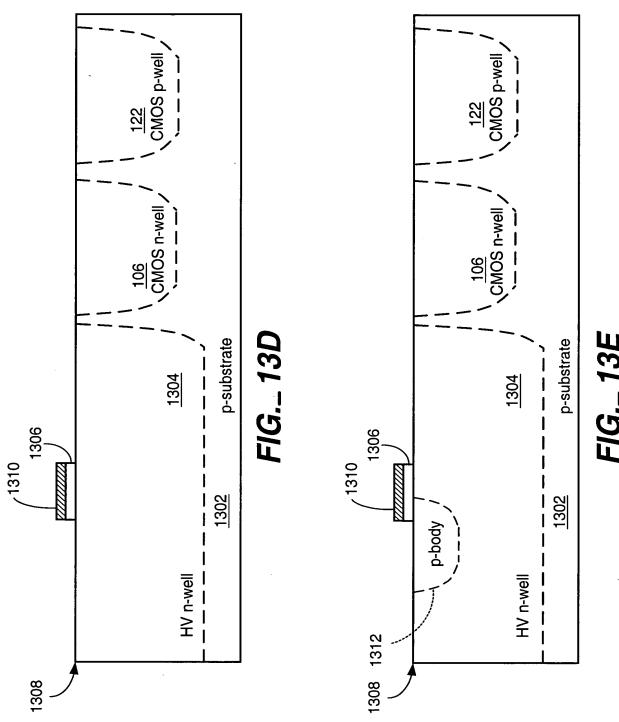


FIG.\_ 12

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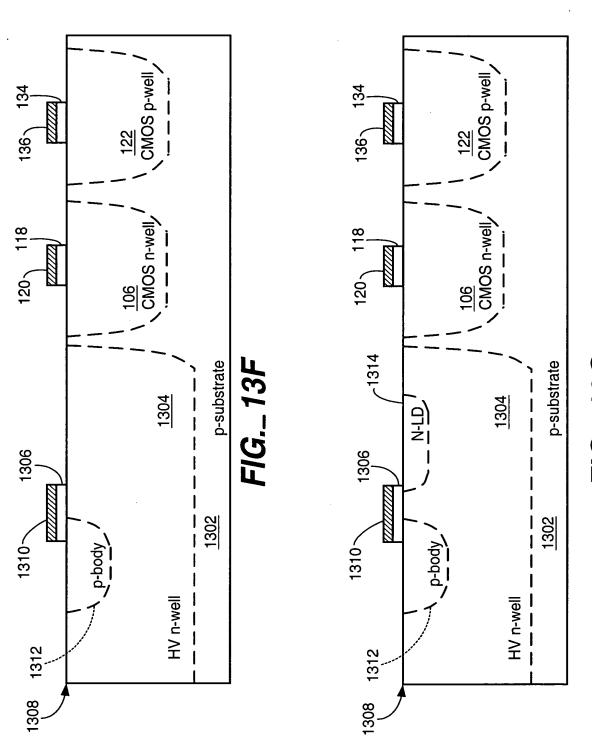


FIG.\_ 13G

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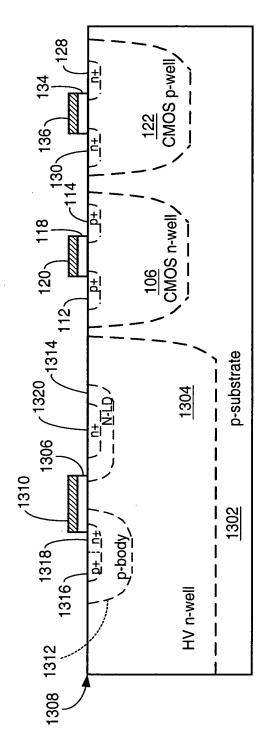


FIG. 13H

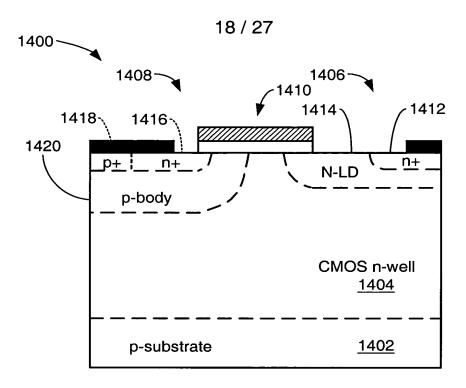


FIG.\_ 14

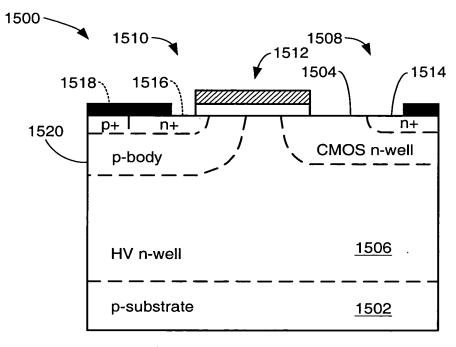


FIG.\_15

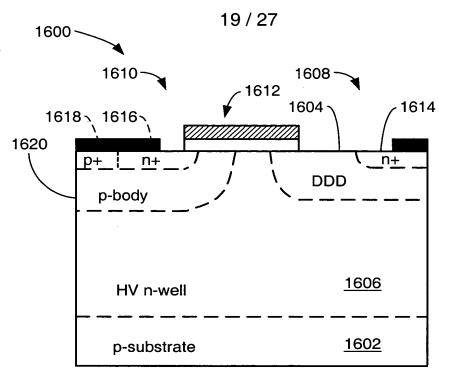


FIG.\_ 16

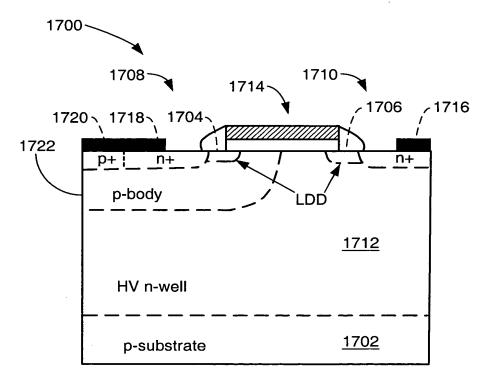


FIG.\_17

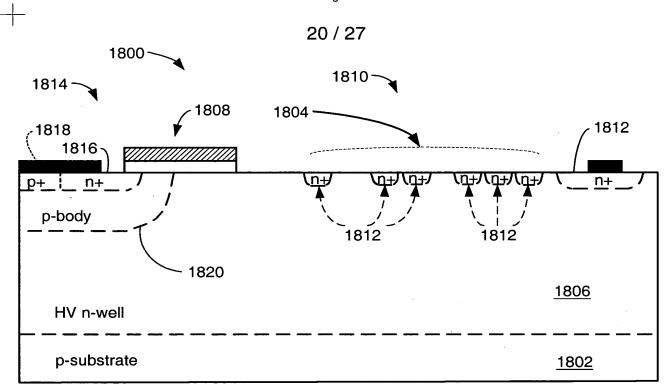


FIG.\_ 18

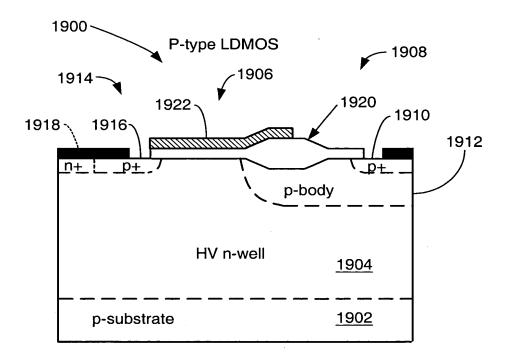


FIG.\_19

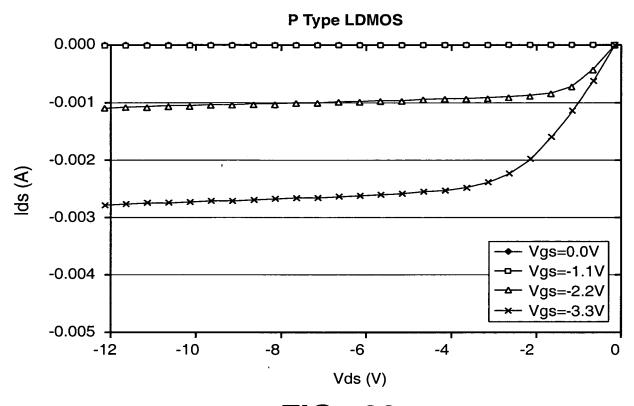


FIG.\_20

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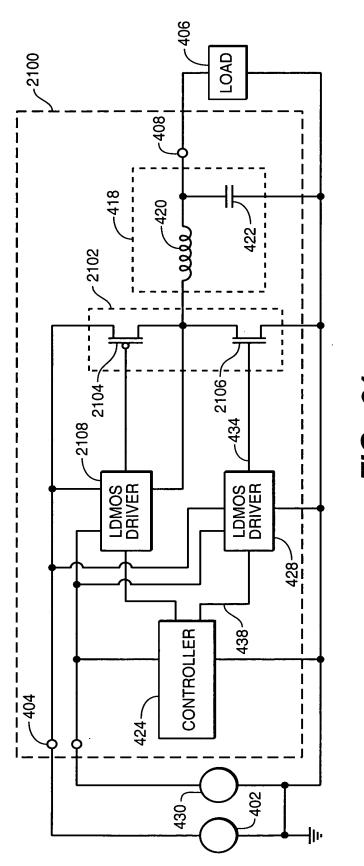
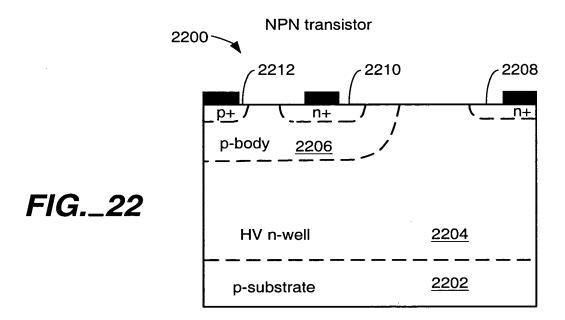
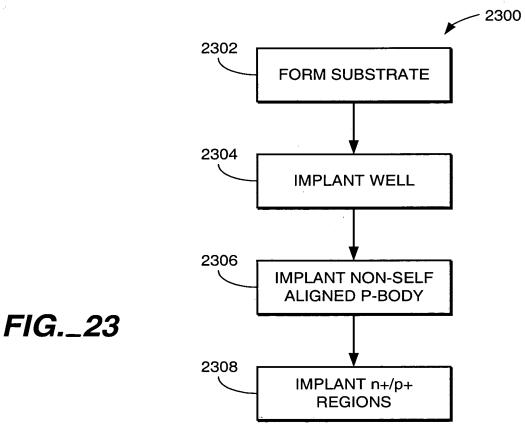
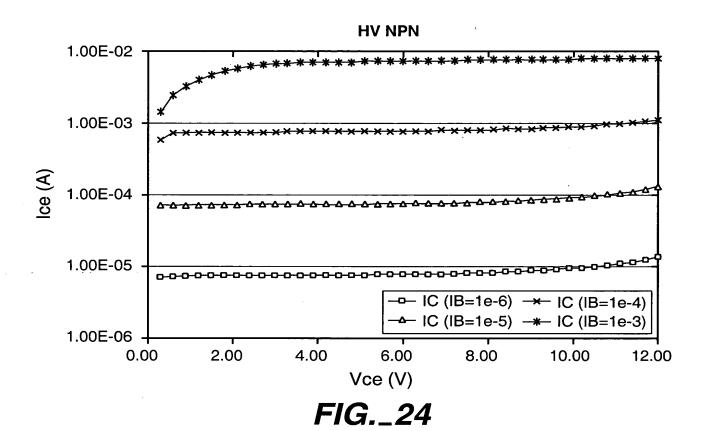


FIG.\_21

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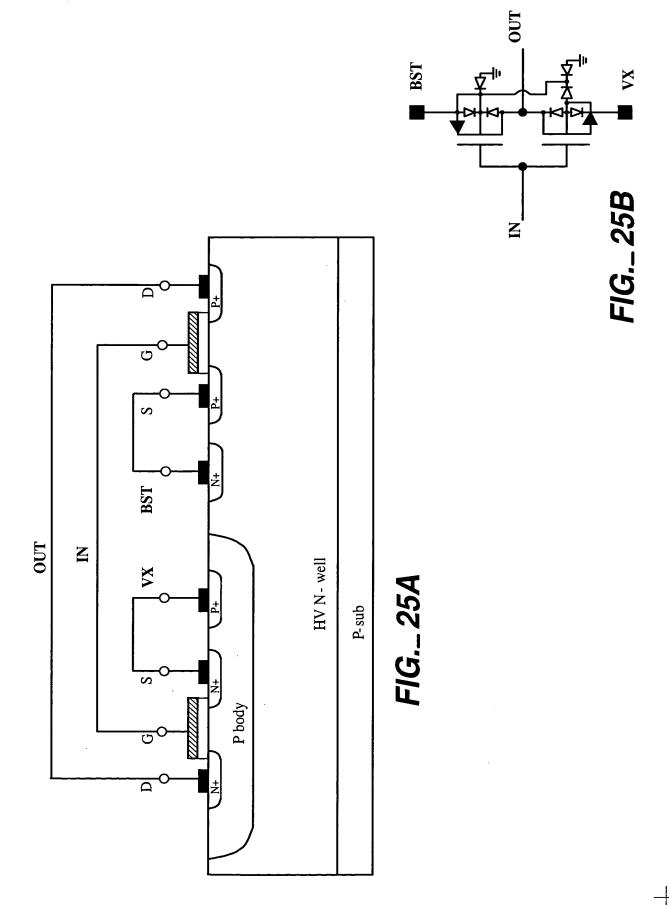


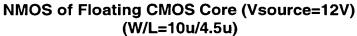




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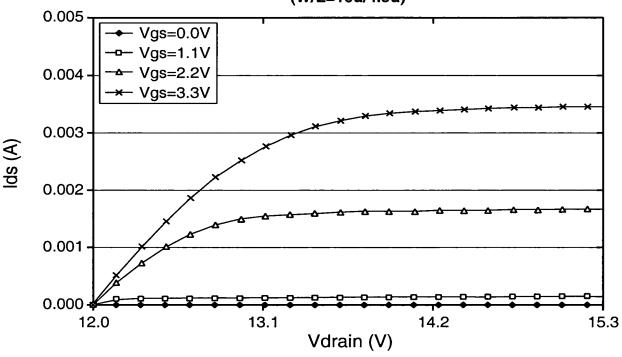
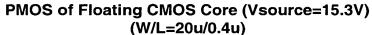


FIG.\_26A



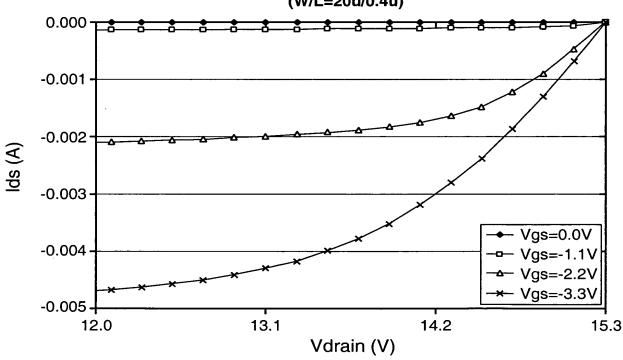


FIG.\_26B

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